

**SILICON NPN PHOTO TRANSISTOR****1、 DESCRIPTIONS:**

- GTR1-PT02AB-TT/TR is a high speed and high sensitive silicon NPN phototransistor with exceptionally stable characteristics and high illumination sensitivity.
- Molded in black epoxy , untinted PCB based SMD package.

**2、 FEATURE:**

- Fast Response Time.
- High Photo Sensitivity.
- Lead Free product, in compliance with RoHS.
- Floor life: 168 hours, MSL 3, acc. J-STD-020

**3、 APPLICATIONS:**

- Infrared Applied System.
- Floppy Disk Drive.
- Opto-Electronic Switch.

**4、 ABSOLUTE MAXIMUM RATINGS AT Ta=25°C**

Parameter	Symbol	Ratings	Unit
Power Dissipation	PD	75	mW
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	30	V
Collector Current	I <sub>C</sub>	20	mA
Emitter-Collector Breakdown Voltage	V <sub>ECO</sub>	5	V
Operating Temperature	Topr	-25~+85	°C
Storage Temperature	Tstg	-30~+105	°C
Soldering Temperature	Tsol	260°C (for 5 sec )	

**5、 TYPICAL ELECTRICAL & OPTICAL CHARACTERISTICS (ta=25°C)**

Parameter	Symbol	Min.	Type	Max.	Unit	Test Condition
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_c=100\mu A$ $E_e=0mW/cm^2$
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5			V	$I_E=100\mu A$ $E_e=0mW/cm^2$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.2	V	$I_c=2mA$ $I_B=100\mu A$
Rise Time	$T_r$		15		$\mu S$	$V_{CE}=5V$ $I_c=1mA$ $R_L=1000\Omega$
Fall Time	$T_f$		15		$\mu S$	
Collector Dark Current	$I_{CEO}$			100	nA	$V_{CE}=10V$ $E_e=0mW/cm^2$
On State Collector Current	$I_{C(on)}$	1.0	3.0	6.0	mA	5V $E_e=1mW/cm^2$ $\lambda_p=940nm$
Peak Wavelength of Sensitive	$\lambda_p$		940		nm	

**6、 RELIABILITY TEST ITEMS AND CONDITIONS:**

NO	Item	Test Conditions	Test Hours/Cycle	Sample Quantity	Test Result
1	Solder Heat	TEMP: 260°C ±3°C	5 SEC	11 pcs	0 DEFECT
2	Temperature Cycle	H:+85°C 180min ↕ 10min L:-25°C 180min	16 cycles	22 pcs	0 DEFECT
3	Thermal Shock	H:+85°C 30min ↕ 30sec L:-25°C 30min	10 cycles	11 pcs	0 DEFECT
4	High Temperature Storage	TEMP: +25°C	1000 HRS	22 pcs	0 DEFECT
5	Low Temperature Storage	TEMP: -25°C	1000 HRS	22 pcs	0 DEFECT
6	High Temperature High Humidity Storage	85°C/85% RH	1000HRS	22 pcs	0 DEFECT

**7、TYPICAL ELECTRO-OPTICAL CHARACTERISTICS CURVES:**

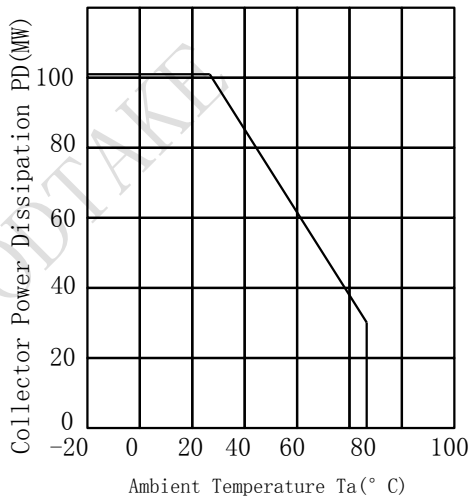


FIG. 1 Collector Pd vs Ta

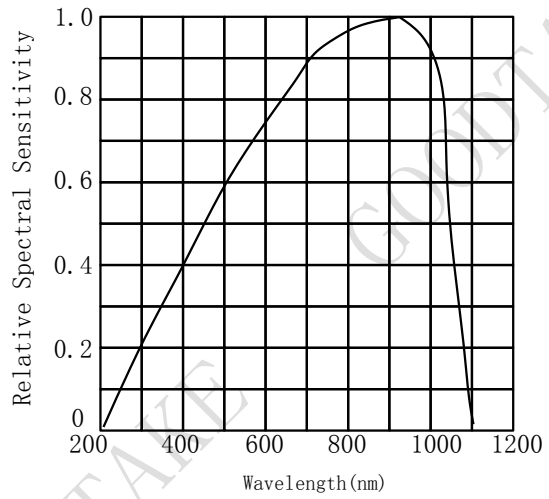


FIG. 2 Spectral Sensitivity

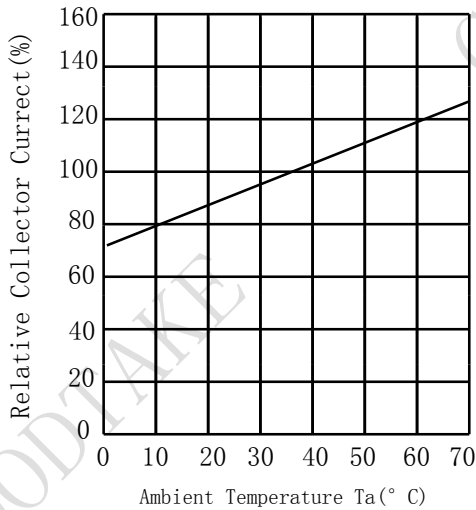


FIG. 3 Relative Ic vs. Ta

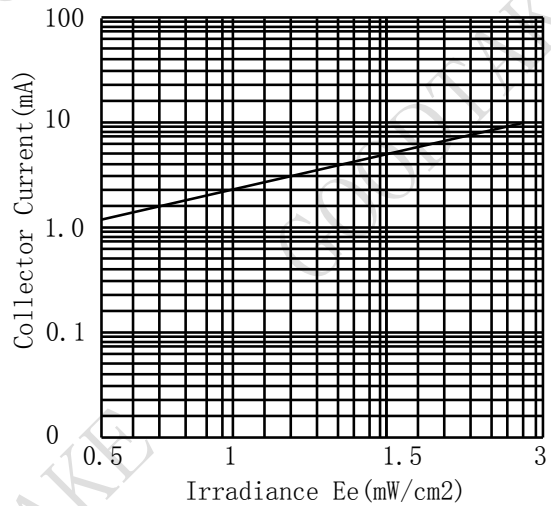


FIG. 4 Ic vs Iv

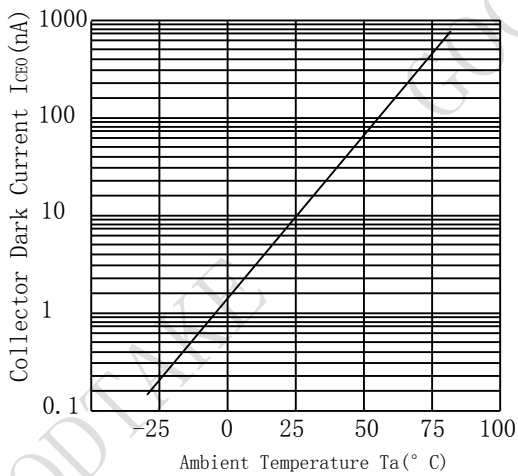
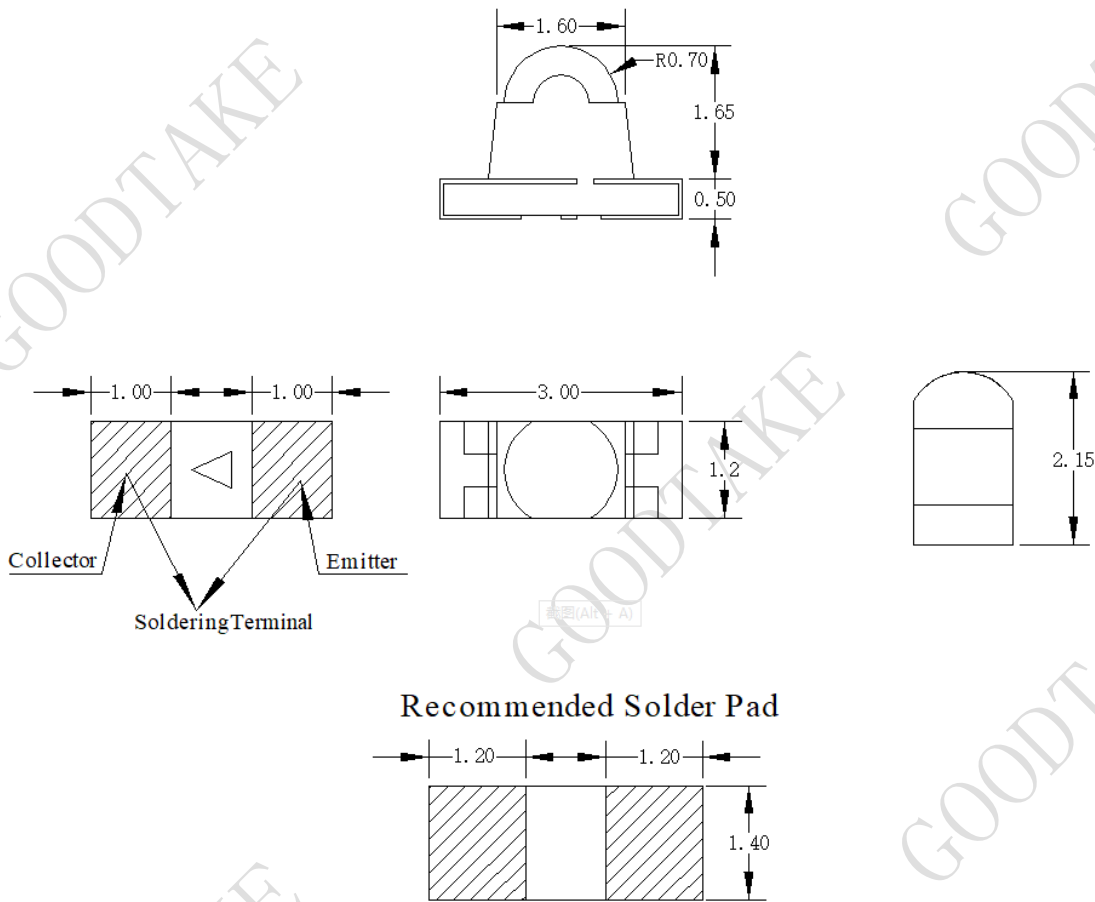


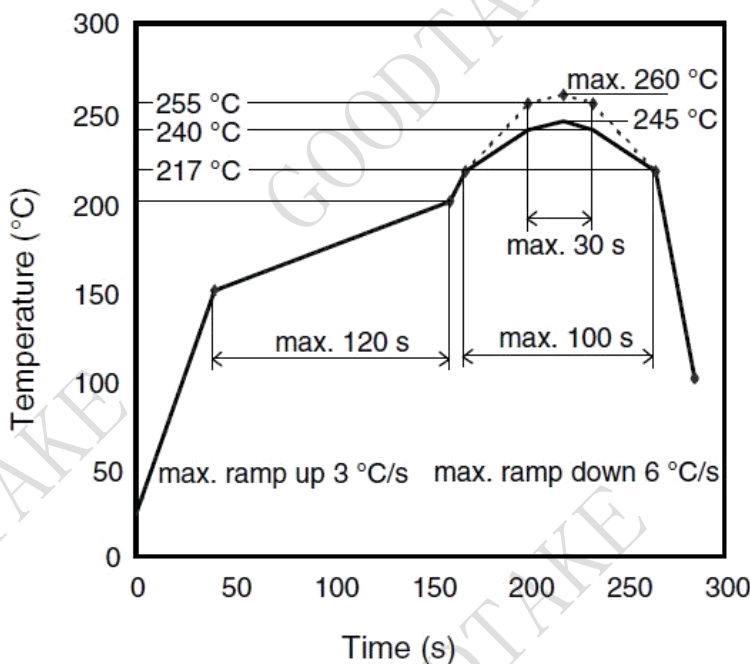
FIG. 5 Id vs Ta

**8、 PACKAGE DIMENSIONS:**



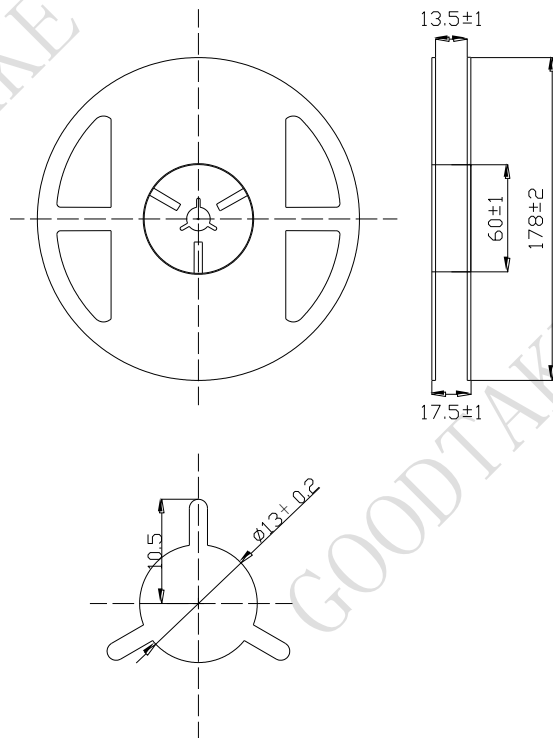
1. All dimensions are in millimeters
2. Tolerance is  $\pm 0.15$  unless otherwise noted

**9、 REFLOW SOLDER PROFIEL:**

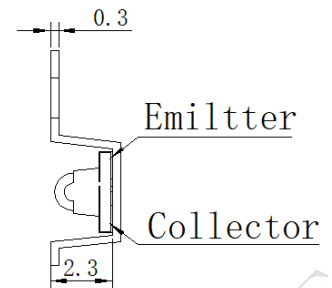
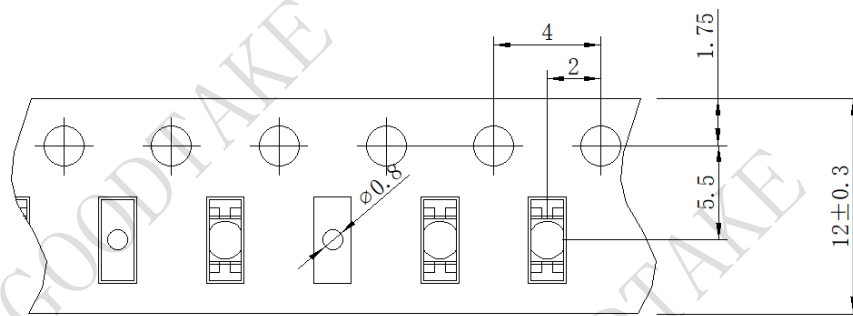


**10. TAPPING AND PACKING SPECIFICATIONS:**

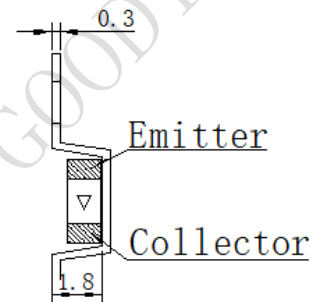
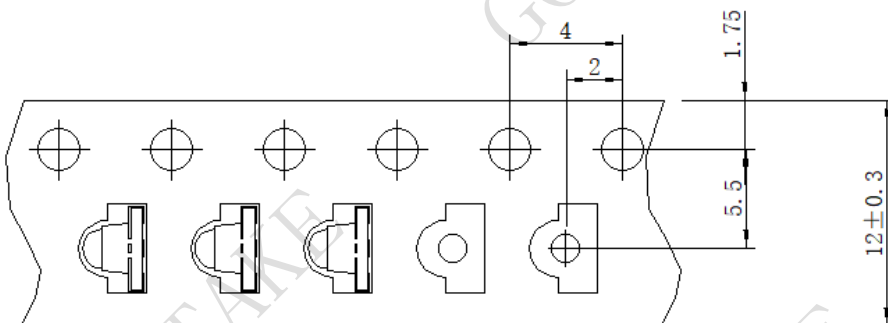
(1) Shape and dimensions of reels: unit in mm



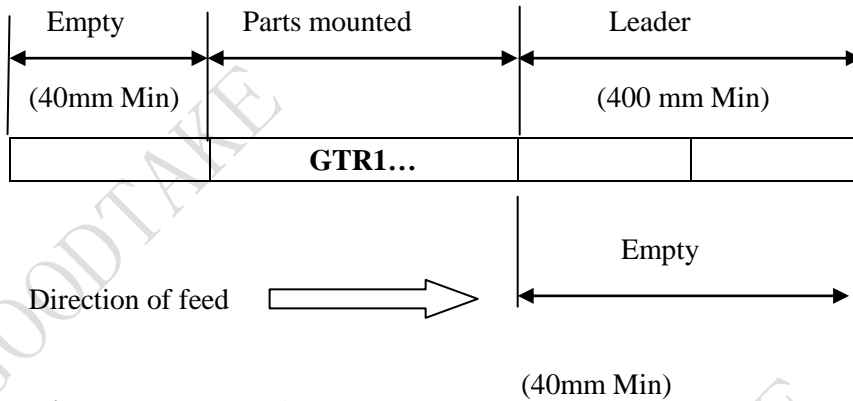
(2) Dimensions of TT tape:



(3) Dimensions of TR tape:

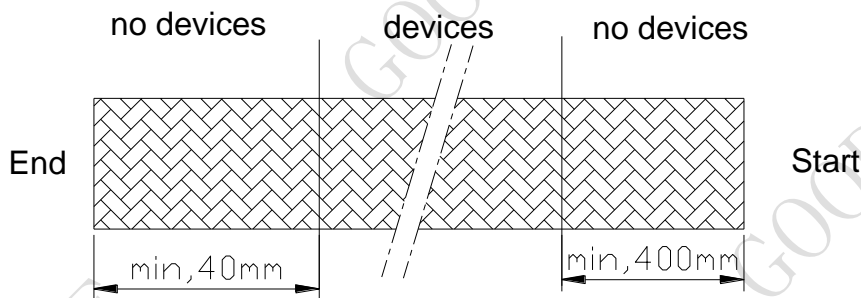


**(4) Configuration of tape**



**(5) Quantity:** 2,000pcs/ reel

**Leader And Trailer Dimensions**



**Antistatic dry packing**

Opto devices in SMD package may be sensitive to moisture. Devices are taped & reeled, sealed in antistatic bag with silica gel desiccants.

Do not open the sealed moisture-proof bag before ready to use. If sealing is void, baking treatment may be required.

**Storage**

**Shelf life** – Devices should be stored in its original packing, in a controlled environment of temperature less than 40 °C and relative humidity below 90%.

Suggested shelf life is 12 months in its original packing.

**Floor life** – MSL3. After opening of the sealed package, the reeled devices should be consumed within 168 hours, in a controlled environment condition of  $T_{amb} < 30\text{ °C}$ ,  $RH = < 60\%$ .

Remaining unused parts should be stored in Dry Box chamber.

**Drying (Baking Process)**

If original packing is voided (such as faded silica gel or exceeded storage time), baking treatment should be performed with the following conditions:-  $T_{storage} = 40 + 5\text{ °C}$ ,  $RH < 5\%$ ,  $time = 192\text{ hours}$ .